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Vishay Siliconix

# N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)			
100	0.0056 at V <sub>GS</sub> = 10 V	131	53.5 nC			
	0.0062 at V <sub>GS</sub> = 7.5 V	129	33.3 110			



### **Ordering Information:**

SUM70060E-GE3 (lead (Pb)-free and halogen-free)

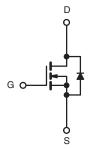
#### **FEATURES**

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



### **APPLICATIONS**

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- · Motor drive switch
- DC/AC inverter
- · Battery management



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	100	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
O. 150 (0.0)	T <sub>C</sub> = 25 °C	1	131	Δ.		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 125 °C		75			
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	240	А			
Avalanche Current	L = 0.1 mH		50			
Single Avalanche Energy <sup>a</sup>	L = 0.1 IIII	E <sub>AS</sub>	125	mJ		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	375 <sup>b</sup>	W		
iviaxiitiutti Fowei Dissipatioti «	T <sub>C</sub> = 125 °C	- FD	125 <sup>b</sup>	T VV		
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W			
Junction-to-Case (Drain)	R <sub>th,IC</sub>	0.75	C/W			

## Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100		
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	2	mA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	90	-	-	Α	
Drain Course On State Resistance 8		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.0046	0.0056		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, I_D = 30 \text{ A}$	-	0.0048	0.0062	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	85	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	3330	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}$	-	1395	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	95	-		
Total Gate Charge <sup>c</sup>	$Q_g$		-	53.5	81	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	14.5	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	13.2	-		
Gate Resistance	$R_g$	f = 1 MHz	0.9	1.9	3.8	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	13	26		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 1.67 $\Omega$	-	22	44	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D\cong 30~A,~V_{GEN}=10~V,~R_g=1~\Omega$	-	27	54		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	9	18		
Drain-Source Body Diode Ratings a	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	240	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V	-	0.86	1.4	٧	
Reverse Recovery Time	t <sub>rr</sub>		-	88	176	ns	
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	5	10	Α	
Reverse Recovery Charge	Reverse Recovery Charge Q <sub>rr</sub>		-	0.22	0.44	μC	

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



100

80

60

40

20

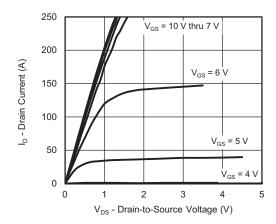
0

T<sub>C</sub> = 25 °C

5.0

gfs - Transconductance (S)

# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### **Output Characteristics**

T<sub>C</sub> = -55 °C

T<sub>C</sub> = 125 °C

25.0

30.0

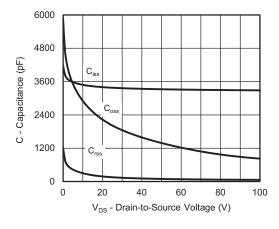


Transconductance

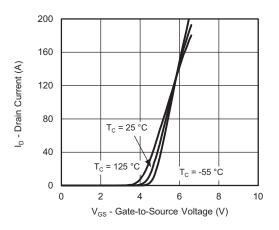
15.0

I<sub>D</sub> - Drain Current (A)

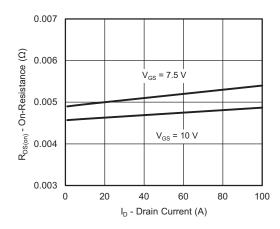
20.0



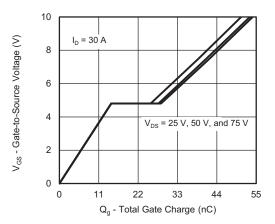
Capacitance



**Transfer Characteristics** 



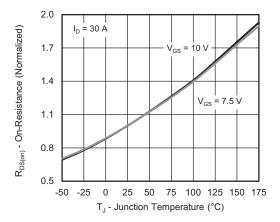
On-Resistance vs. Drain Current



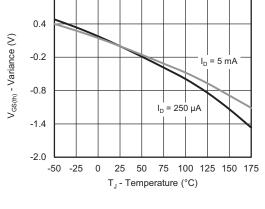
**Gate Charge** 



# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

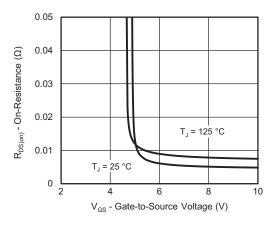


On-Resistance vs. Junction Temperature

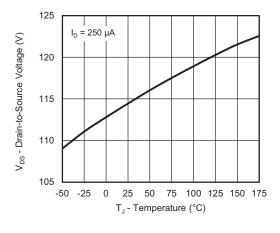


1.0

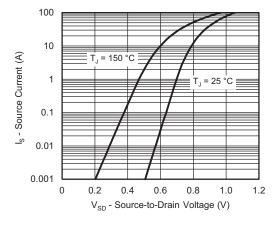
**Threshold Voltage** 



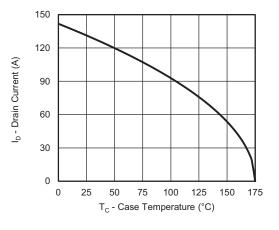
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



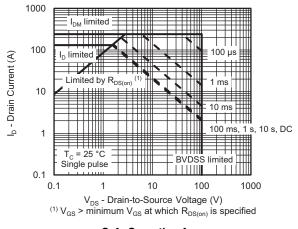
**Source Drain Diode Forward Voltage** 

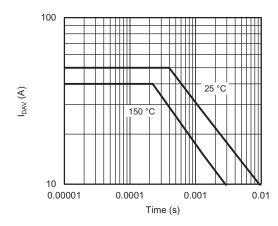


**Current De-Rating** 



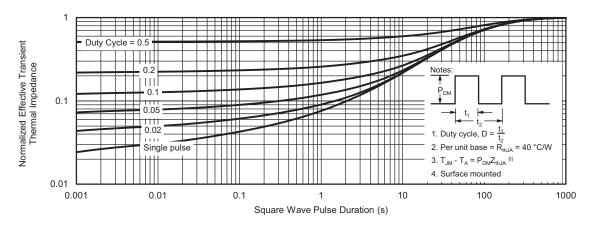
# **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





Safe Operating Area

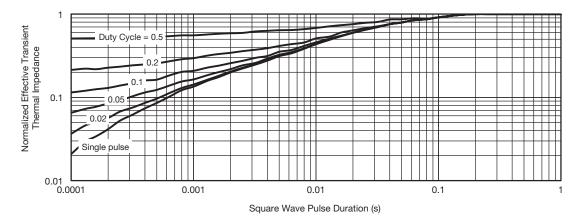
I<sub>DAV</sub> vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



# THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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# TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072 0.078		1.829 1.981		
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010	BSC	0.254 BSC		
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





# RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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